

## ABSTRACT OF THE DISCLOSURE

A semiconductor light emitting device includes a semiconductor substrate; a stacked semiconductor structure formed on the semiconductor substrate; a striped ridge structure; and a semiconductor current confinement layer provided on a side surface of the striped ridge structure. The stacked semiconductor structure includes a first semiconductor clad layer, a semiconductor active layer, a second semiconductor clad layer, and a semiconductor etching stop layer. The striped ridge structure includes a third semiconductor clad layer, a semiconductor intermediate layer, and a semiconductor cap layer. The striped ridge structure is provided on the semiconductor etching stop layer. An interface between the semiconductor current confinement layer and the semiconductor etching stop layer and an interface between the semiconductor current confinement layer and the striped ridge structure each have a content of impurities of less than  $1 \times 10^{17}/\text{cm}^3$ .